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Jordan Bouaziz, Bertrand Vilquin, Pedro Rojo Romeo, Nicolas Baboux, Bruno Masenelli. Deposition of doped and undoped HfO₂ for fast and low energy consumption ferroelectric devices. 6th International Conference SENSO Workshop, Jun 2018, Gardanne, France. hal-02506625

HAL Id: hal-02506625

<https://hal.science/hal-02506625>

Submitted on 13 Mar 2020

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